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June 2014



FQA70N10

N-Channel QFET® MOSFET

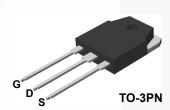
100 V, 70 A, 23 m Ω

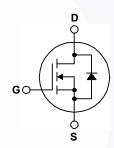
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 70 A, 100 V, $R_{DS(on)} = 23 \text{ m}\Omega$ (Max) @ $V_{GS} = 10 \text{ V}$, $I_D = 35 \text{ A}$
- Low Gate Charge (Typ. 85 nC)
- Low Crss (Typ. 150 pF)
- · 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter		FQA70N10	Unit
V_{DSS}	Drain-Source Voltage		100	V
I _D	Drain Current - Continuous (T _C = 25°C)		70	Α
	- Continuous (T _C = 100°C	;)	49.5	Α
I _{DM}	Drain Current - Pulsed	(Note 1)	280	Α
V _{GSS}	Gate-Source Voltage		± 25	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	1300	mJ
I _{AR}	Avalanche Current	(Note 1)	70	Α
E _{AR}	Repetitive Avalanche Energy	(Note 1)	21.4	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		6.0	V/ns
P_{D}	Power Dissipation (T _C = 25°C)		214	W
	- Derate above 25°C		1.43	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FQA70N10	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.7	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

Package Marking and Ordering Information

Device Marking Device		Package	Reel Size	Tape Width	Quantity	
FQA70N10	FQA70N10	TO-3PN	-	-	30	

Electrical Characteristics

T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Uni
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.1		V/°(
I _{DSS}	Zana Oata Valta va Busin Ouwant	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ
	Zero Gate Voltage Drain Current	V _{DS} = 80 V, T _C = 150°C			10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 25 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -25 V, V _{DS} = 0 V			-100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0		4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 35 A		0.019	0.023	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 35 A		48		S
•	ic Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		2500	3300	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		720	940	pF
C _{rss}	Reverse Transfer Capacitance			150	200	pF
Switchi	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 50 V, I _D = 70 A,		30	70	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$		470	950	ns
$t_{d(off)}$	Turn-Off Delay Time	3		130	270	ns
t _f	Turn-Off Fall Time	(Note 4)		160	330	ns
Qg	Total Gate Charge	V _{DS} = 80 V, I _D = 70 A,	/	85	110	nC
^	0-4- 0	- DO TO -		40		

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current		 	70	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		 	280	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 70 A	 	1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 70 A,	 110	//	ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs	 430		nC

 V_{GS} = 10 V

 Q_{gd}

- Notes: 1. Repetitive Rating : Pulse width limited by maximum junction temperature 2. L = 0.4mH, I_{AS} = 70A, V_{DD} = 25V, R_{G} = 25 Ω , Starting T_{J} = 25°C 3. I_{SD} \leq 70A, di/dt \leq 300A/ μ s, V_{DD} \leq BV $_{DSS}$, Starting T_{J} = 25°C 4. Essentially independent of operating temperature

Gate-Source Charge

Gate-Drain Charge

16

42

(Note 4)

nC

nC

Typical Characteristics

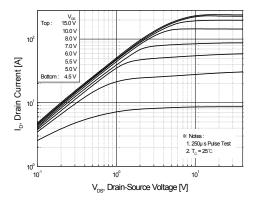


Figure 1. On-Region Characteristics

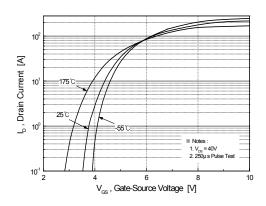


Figure 2. Transfer Characteristics

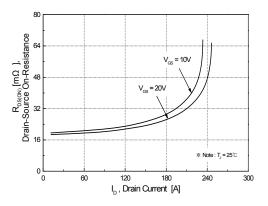


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

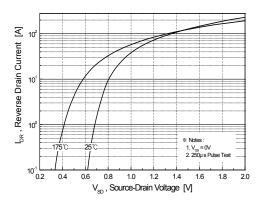


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

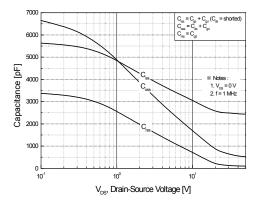


Figure 5. Capacitance Characteristics

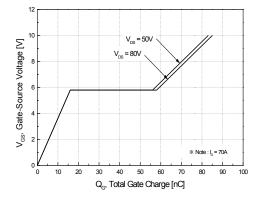


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

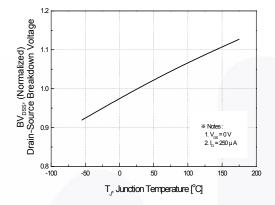


Figure 7. Breakdown Voltage Variation vs. Temperature

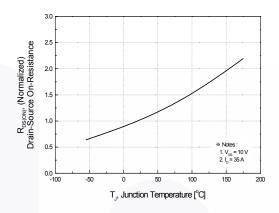


Figure 8. On-Resistance Variation vs. Temperature

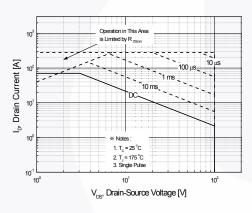


Figure 9. Maximum Safe Operating Area

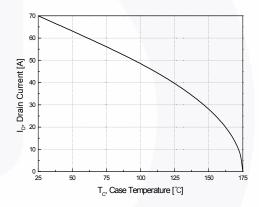


Figure 10. Maximum Drain Current vs. Case Temperature

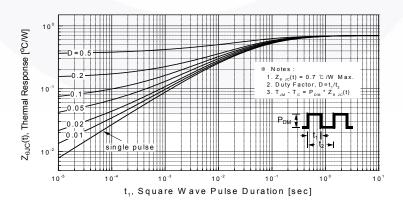


Figure 11. Transient Thermal Response Curve



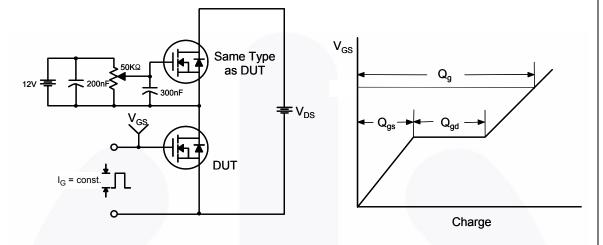


Figure 13. Resistive Switching Test Circuit & Waveforms

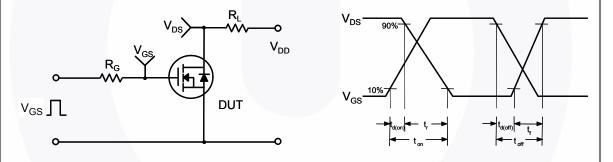
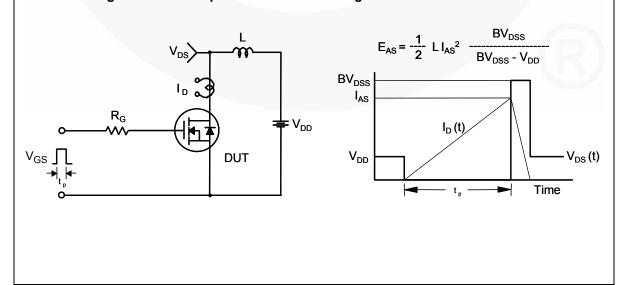
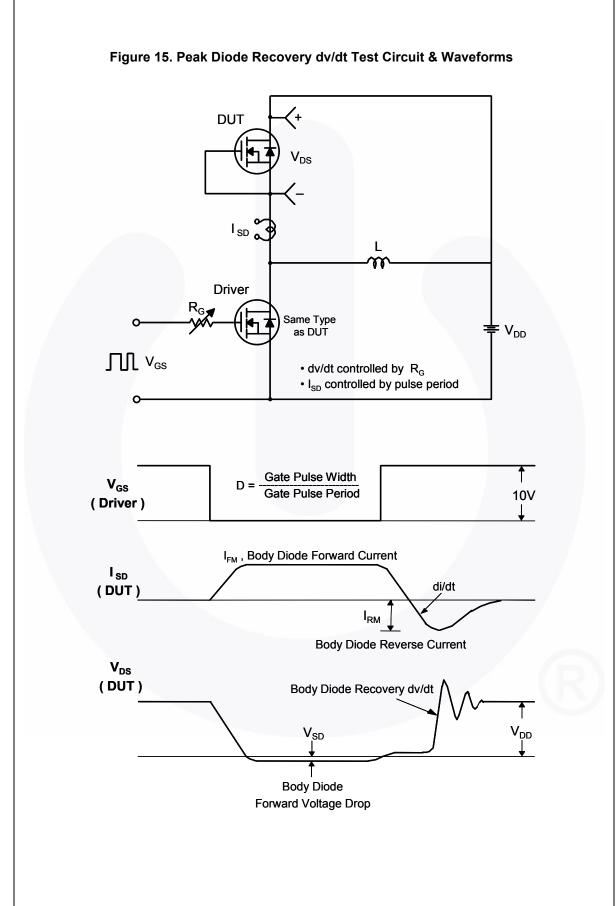


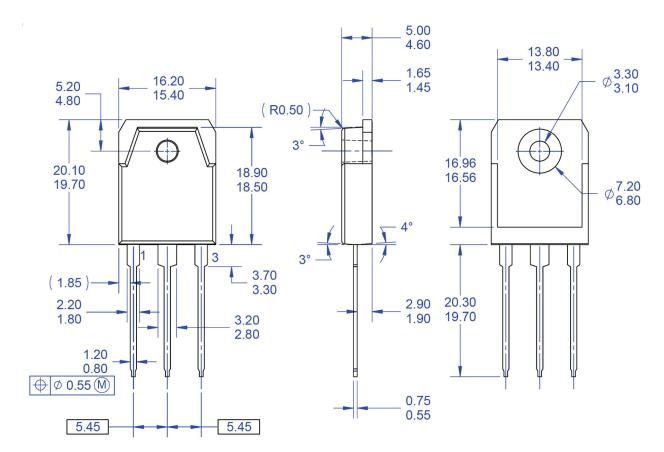
Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

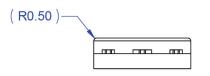




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Mechanical Dimensions





NOTES: UNLESS OTHERWISE SPECIFIED

- A) THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
 C) DIMENSION AND TOLERANCING PER
- ASME14.5-2009.
- D) DIMENSIONS ARE EXCLUSSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSSIONS.
- E) DRAWING FILE NAME: TO3PN03AREV1.
- F) FAIRCHILD SEMICONDUCTOR.

Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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